

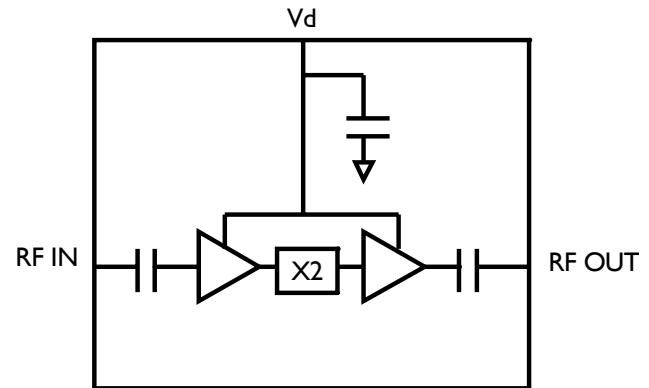
Features

- Integrated Gain, Doubler and Driver Stages
- Self-biased Architecture
- +21.0 dBm Output Saturated Power
- 40.0 dBc Fundamental Suppression
- On-Chip ESD Protection
- 100% On-Wafer RF, DC & Output Power Testing
- 100% Visual Inspection to MIL-STD-883 Method 2010
- RoHS* Compliant and 260°C Reflow Compatible

Description

M/A-COM Tech's 13.5-17.0 / 27.0-34.0 GHz GaAs MMIC doubler integrates a gain stage, passive doubler and driver amplifier onto a single device. The XX1007-BD has a self-biased architecture requiring a single positive supply (+5V) only and integrated on-chip bypassing capacitor eliminating the need for external capacitor. This MMIC uses M/A-COM Tech's GaAs PHEMT device model technology, and is based upon electron beam lithography to ensure high repeatability and uniformity. The chip has integrated ESD structures for protection and surface passivation to protect and provide a rugged part with backside via holes and gold metallization to allow either a conductive epoxy or eutectic solder die attach process. This device is well suited for Millimeter wave Point-to-Point Radio, LMDS, SATCOM and VSAT applications.

Functional Block Diagram



Absolute Maximum Ratings

Parameter	Absolute Max.
Supply Voltage (Vd)	+6.0 VDC
Supply Current (Id)	300 mA
Gate Bias Voltage (Vg)	+0.3 VDC
Input Power (RF Pin)	TBD
Storage Temperature (Tstg)	-65 to +165 °C
Operating Temperature (Ta)	-55 to MTTF Table ¹
Channel Temperature (Tch)	MTTF Table ¹

- (1) Channel temperature directly affects a device's MTTF. It is recommended to keep channel temperature as low as possible to maximize lifetime.

Ordering Information

Part Number	Package
XX1007-BD-000V	"V" - vacuum release gel paks
XX1007-BD-EV1	evaluation module

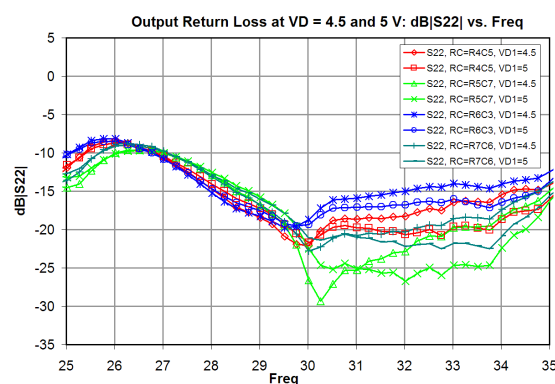
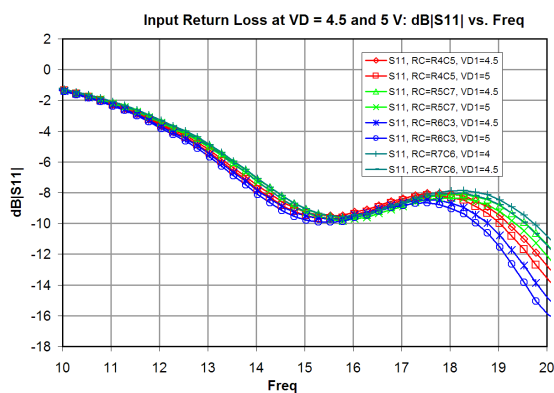
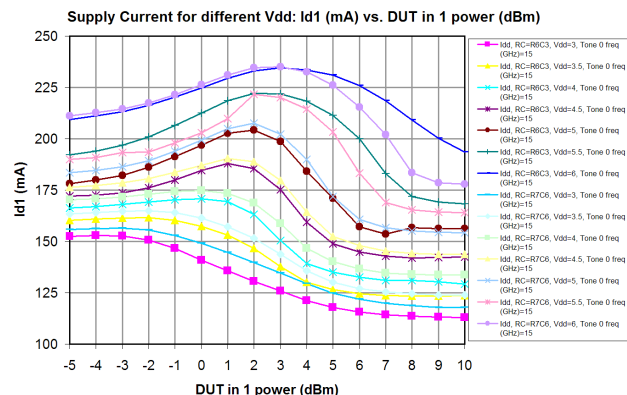
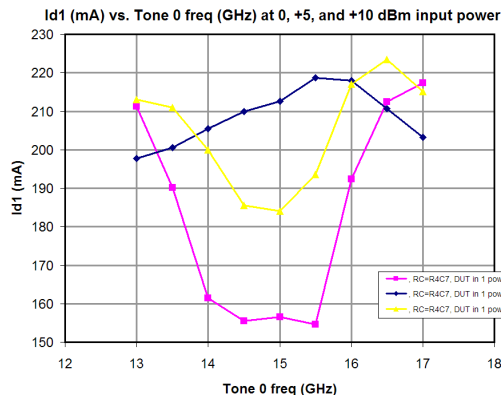
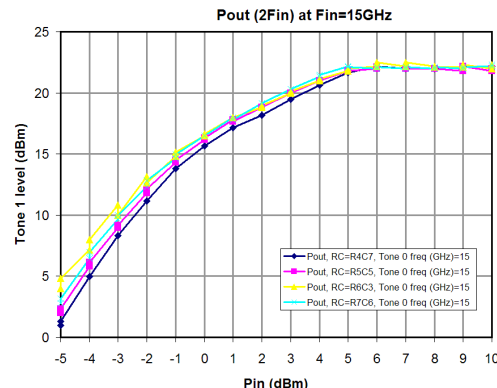
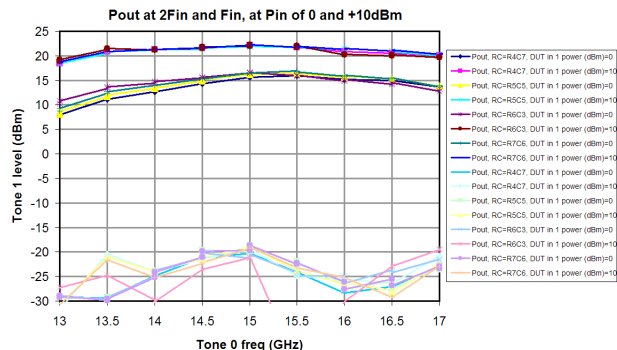
Doubler
13.5-17.0/27.0-34.0 GHz

Rev. V1
MimiX Broadband

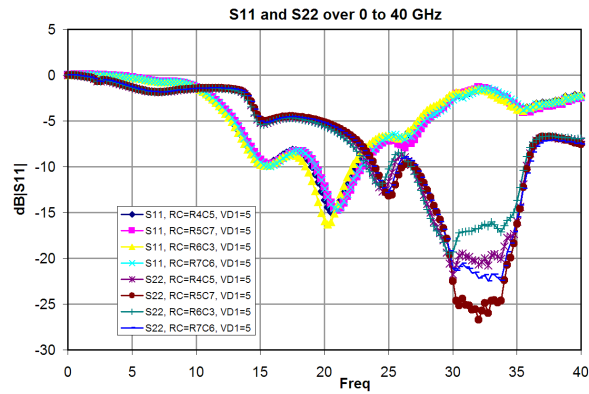
Electrical Specifications: 13.5-17 GHz (fin) (Ambient Temperature T = 25°C)

Parameter	Units	Min.	Typ.	Max.
Output Frequency Range (fout)	GHz	27.0	-	34.0
Input Return Loss (S11)	dB	-	-8.0	-
Output Return Loss (S22)	dB	-	-10.0	-
Fundamental Level at the Output	dBc	-28.0	-35.0	-
RF Input Power (RF Pin)	dBm	-	+8.0	-
Output Power at 8.0 dBm Pin (Pout)	dBm	+16.0	+21.0	-
Drain Bias Voltage (Vd)	VDC	-	+5.0	+5.5
Supply Current (Id1,2,3) (Vd=5.0V Typical)	mA	-	200	240

Typical Performance Curves



Typical Performance Curves

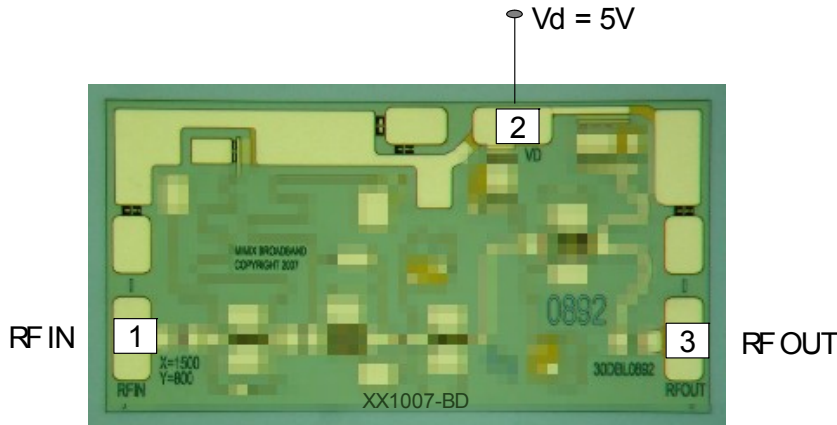


XX1007-BD

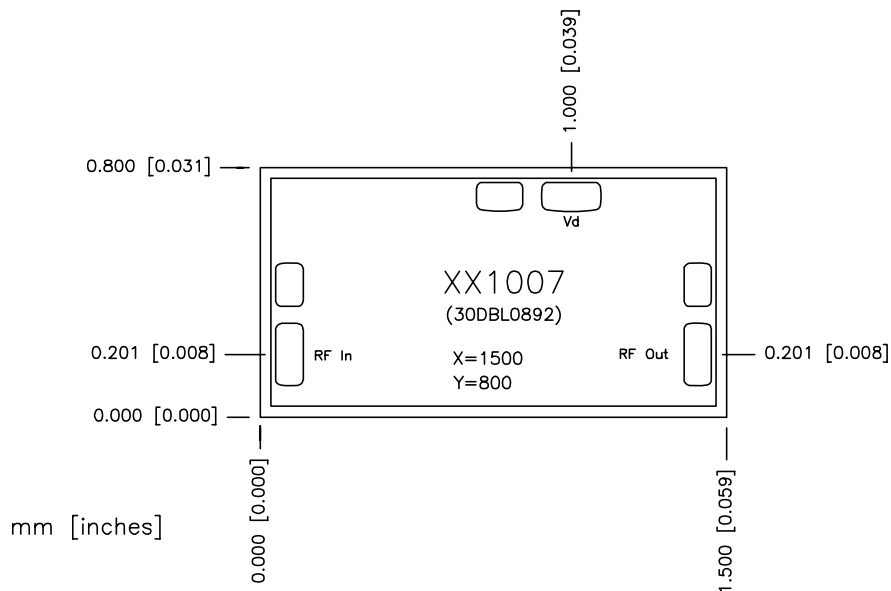
Doubler
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Bias Arrangement



Physical Dimensions



Doubler
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MTTF Tables (TBD)

These numbers were calculated based on accelerated life test information and thermal model analysis received from the fabricating foundry.

Backplate Temperature	Channel Temperature	Rth	MTTF Hours	FITs
55 deg Celsius	deg Celsius	C/W	E+	E+
75 deg Celsius	deg Celsius	C/W	E+	E+
95 deg Celsius	deg Celsius	C/W	E+	E+

Bias Conditions: Vd=5.0V, Id=200mA

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these class 2 devices.